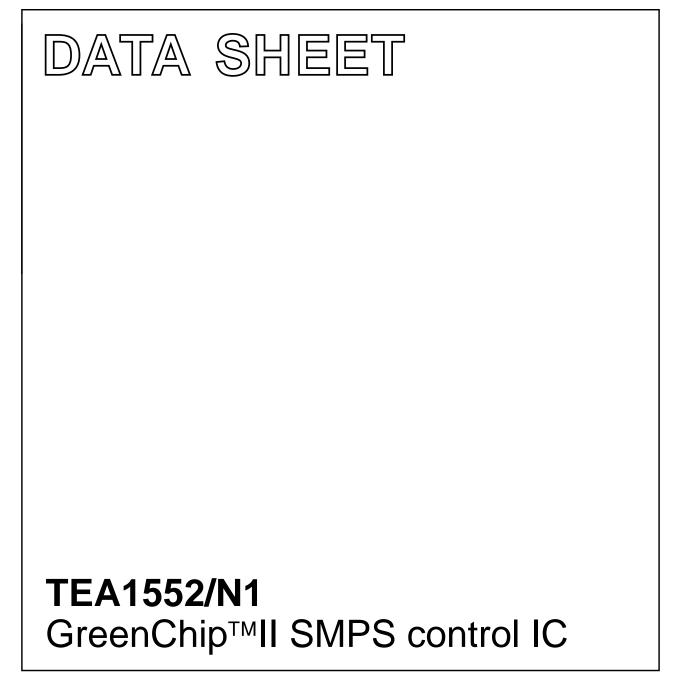
INTEGRATED CIRCUITS



Preliminary specification File under Integrated Circuits, IC11 2002 Feb 05

Version 1.4





TEA1552/N1

FEATURES

Distinctive features

- Universal mains supply operation (70 to 276 V AC).
- High level of integration, giving a very low external component count.

Green features

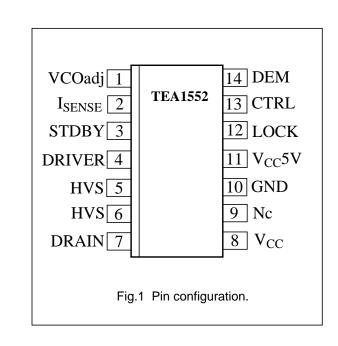
- Valley/zero voltage switching for minimum switching losses.
- Efficient quasi-resonant operation at high power levels.
- Frequency reduction at low power standby for improved system efficiency (<3 W).
- Cycle skipping mode at very low loads.
 Pin <300mW at no-load operation for a typical adapter application.
- On-chip start-up current source.
- Stand-by indication pin to indicate low output power consumption.

Protection features

- · Safe restart mode for system fault conditions.
- Continuous mode protection by means of demagnetization detection (zero switch-on current).
- Accurate and adjustable overvoltage protection (latched).
- Short winding protection.
- Undervoltage protection (foldback during overload).
- Overtemperature protection (latched).
- Low and adjustable overcurrent protection trip level.
- Soft (re)start.
- Mains voltage-dependent operation-enabling level.
- General purpose input for lock protection.

APPLICATIONS

Typical application areas are adapters and Chargers (e.g. for laptops, camcorders and printers) and all applications that demand an efficient and cost-effective solution up to 250 W.



PINNING

SYMBOL	PIN	DESCRIPTION
VCOadj	1	VCO adjustment input
I _{sense}	2	programmable current sense input
STDBY	3	Stand-by indication / control output
DRIVER	4	gate driver output
HVS	5	high voltage safety spacer, not connected
HVS	6	high voltage safety spacer, not connected
DRAIN	7	drain of external MOS switch, input for start-up current and valley sensing
V _{CC}	8	supply voltage
Nc	9	not connected
GND	10	ground
V _{CC} 5V	11	5V output
LOCK	12	Lock input
CTRL	13	control input
DEM	14	input from auxiliary winding for demagnetization timing, OVP and OPP

ORDERING INFORMATION

ТҮРЕ	PACKAGE				
NUMBER	NAME	DESCRIPTION VERSION			
TEA1552	SO14	plastic small outline package; 14 leads SOT10			

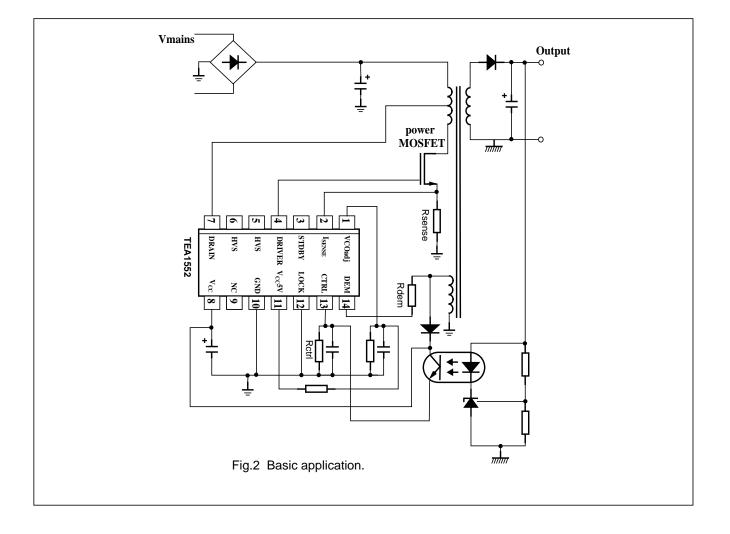
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GENERAL DESCRIPTION

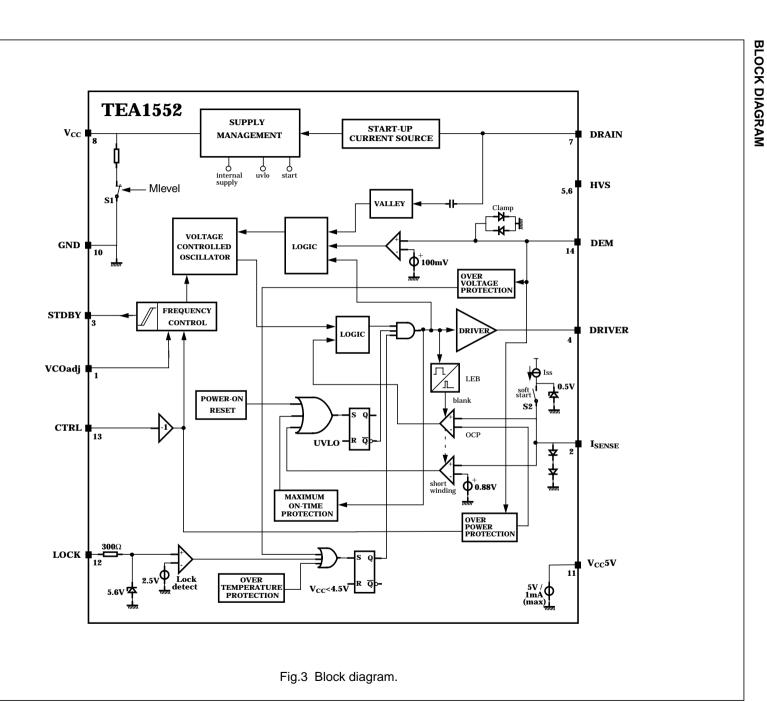
The GreenChip[™]II is the second generation of green Switched Mode Power Supply (SMPS) controller ICs operating directly from the rectified universal mains. A high level of integration leads to a cost effective power supply with a very low number of external components.

The special built-in green functions allow the efficiency to be optimum at all power levels. This holds for quasi-resonant operation at high power levels, as well as fixed frequency operation with valley switching at medium power levels. At low power (standby) levels, the system operates at reduced frequency and with valley detection. The proprietary high voltage BCD800 process makes direct start-up possible from the rectified mains voltage in an effective and green way. A second low voltage BICMOS IC is used for accurate, high speed protection functions and control.

Highly efficient, reliable supplies can easily be designed using the GreenChip™II controller.



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FUNCTIONAL DESCRIPTION

The TEA1552 is the controller of a compact flyback converter, with the IC situated at the primary side. An auxiliary winding of the transformer provides demagnetization detection and powers the IC after start-up.

The TEA1552 operates in multi modes.

The next converter stroke is started only after demagnetization of the transformer current (zero current switching), while the drain voltage has reached the lowest voltage to prevent switching losses (green function). The primary resonant circuit of primary inductance and drain capacitor ensures this quasi-resonant operation. The design can be optimized in such a way that zero voltage switching can be reached over almost the universal mains range.

To prevent very high frequency operation at lower loads, the quasi-resonant operation changes smoothly in fixed frequency PWM control.

At very low power (standby) levels, the frequency is controlled down, via the VCO, to a minimum frequency of about 25 kHz.

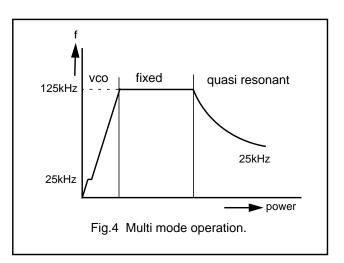
Start-up, mains enabling operation level and undervoltage lock out (see Figs. 11 and 12)

Initially, the IC is self supplying from the rectified mains voltage via pin DRAIN. Supply capacitor C_{VCC} is charged by the internal start-up current source to a level of about 4 V or higher, depending on the drain voltage. Once the drain voltage exceeds the M-level (mains-dependent operation-enabling level), the start-up current source will continue charging capacitor C_{VCC} (switch S1 will be opened), see Fig.3. The IC will activate the power converter as soon as the voltage on pin V_{CC} passes the $V_{CC(start)}$ level. The IC supply is taken over by the auxiliary winding as soon as the output voltage reaches its intended level and the IC supply from the mains voltage is subsequently stopped for high efficiency operation (green function).

The moment the voltage on pin V_{CC} drops below the V_{UVLO} (undervoltage lock out) level, the IC stops switching and enters a safe restart from the rectified mains voltage. Inhibiting the auxiliary supply by external means causes the converter to operate in a stable, well-defined burst mode.

Supply management

All (internal) reference voltages are derived from a temperature compensated, on-chip band gap circuit.



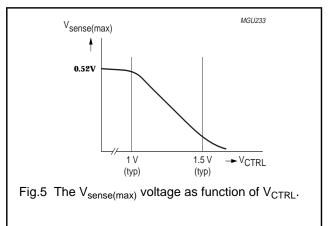
Current mode control

Current mode control is used for its good line regulation behaviour.

The 'on-time' is controlled by the internally inverted control pin voltage, which is compared with the primary current information. The primary current is sensed across an external resistor. The driver output is latched in the logic, preventing multiple switch-on.

The internal control voltage is inversely proportional to the external control pin voltage, with an offset of 1.5 V. This means that a voltage range from 1 to 1.5 V on pin CTRL will result in an internal control voltage range from 0.5 to 0 V (a high external control voltage results in a low duty cycle).

Oscillator

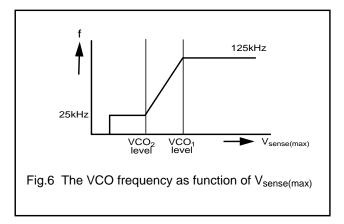


The maximum fixed frequency of the oscillator is set by an internal current source and capacitor. The maximum frequency is reduced once the control voltage enters the

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GreenChip™II SMPS control IC

VCO control window. Then, the maximum frequency changes linearly with the control voltage until the minimum frequency is reached (see Figs 5 and 6).



VCO adjust

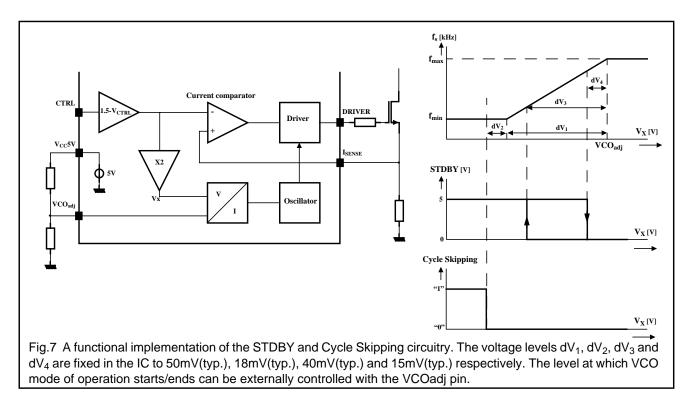
The VCOadj pin can be used to set the VCO operation point. As soon as the peak voltage on the sense resistor is controlled below half the voltage on the VCOadj pin (VCO₁ level), frequency reduction will start (The actual peak voltage on sense will be somewhat higher due to switch-off delay) (see Fig.7). The frequency reduction will stop about 25mV lower (VCO₂ level), when the minimum frequency is reached.

Cycle Skipping

At very low power levels, a cycle skipping mode will be activated. A high control voltage will reduce the switching frequency to a minimum of 25kHz. If the voltage on the control pin is raised even more, switch-on of the external power MOSFET will be inhibited until the voltage on the control pin has dropped to a lower value again (see Fig.7).

For system accuracy, not the absolute voltage on the control pin will trigger the cycle skipping mode. In stead, a signal derived from the internal VCO will be used.

Note 1: If the no-load requirement of the system is such that the output voltage can be regulated to its intended level at a switching frequency of 25kHz or above, the cycle skipping mode will not be activated.



STDBY output

The STDBY output pin can be used to drive an external NPN or FET (Voltage V_{STDBY}=5V) in order to e.g. switch off a PFC circuit. The STDBY output is activated by the internal VCO: as soon as the VCO has reduced the switching frequency to (almost) the minimum frequency of 25kHz, the STDBY output will be activated (see Fig.7). The STDBY output will go low again as soon as the VCO allows a switching frequency close to the maximum frequency of 125kHz

Demagnetization

The system will be in discontinuous conduction mode all the time. The oscillator will not start a new primary stroke until the secondary stroke has ended.

Demagnetization features a cycle-by-cycle output short-circuit protection by immediately lowering the frequency (longer off-time), thereby reducing the power level.

Demagnetization recognition is suppressed during the first t_{suppr} time. This suppression may be necessary in applications where the transformer has a large leakage inductance and at low output voltages/start-up.

Over Voltage Protection (OVP)

An OVP mode is implemented in the GreenChip[™] series. For the TEA1552, this works by sensing the auxiliary voltage via the current flowing into pin DEM during the secondary stroke. The auxiliary winding voltage is a well-defined replica of the output voltage. Any voltage spikes are averaged by an internal filter.

If the output voltage exceeds the OVP trip level, the OVP circuit switches the power MOSFET off. Next, the controller waits until the UVLO level is reached on pin V_{CC} . When V_{CC} drops to UVLO, capacitor C_{VCC} will be recharged to the V_{start} level, however the IC will not start switching again. Subsequently, Vcc will drop again to the UVLO level, etc.

Operation only recommences when the Vcc voltage drops below a level of about 4.5 V (practically when the Vmains has been disconnected for a short period).

The output voltage at which the OVP function trips, $V_{0(OVP)}$ can be set by the demagnetization resistor, R_{DFM} :

$$V_{o(OVP)} = \frac{N_s}{N_{aux}} \times (I_{(OVP)(DEM)} \times R_{DEM} + V_{clamp(DEM)(pos)})$$

Where Ns is the number of secondary turns and Naux is the number of auxiliary turns of the transformer.

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Current Iref is internally trimmed.

The value of the demagnetization resistor (R_{DEM}) can be adjusted to the turns ratio of the transformer, thus making an accurate OVP possible.

Valley switching (see Fig.8)

A new cycle starts when the power switch is switched on. After the 'on-time' (which is determined by the 'sense' voltage and the internal control voltage), the switch is opened and the secondary stroke starts. After the secondary stroke, the drain voltage shows an oscillation

with a frequency of approximately $\frac{1}{(2\times\pi\times\sqrt{(L_n\times C_d)})}$

where L_p is the primary self inductance of the transformer and C_d is the capacitance on the drain node.

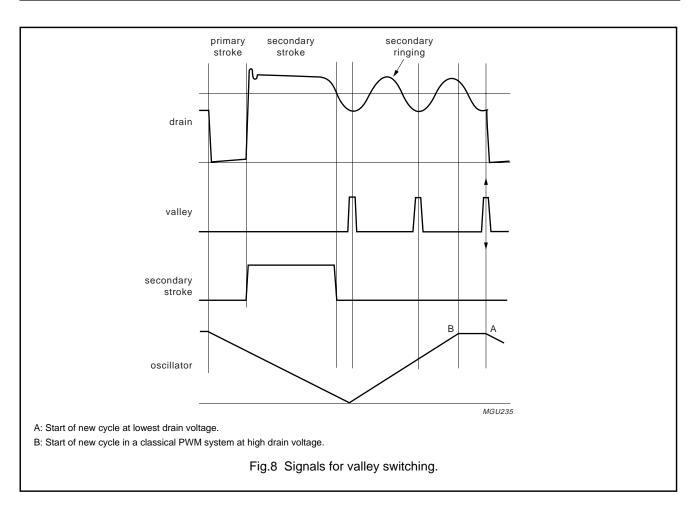
As soon as the oscillator voltage is high again and the secondary stroke has ended, the circuit waits for the lowest drain voltage before starting a new primary stroke. This method is called valley detection. Figure 8 shows the drain voltage together with the valley signal, the signal indicating the secondary stroke and the oscillator signal.

In an optimum design, the reflected secondary voltage on the primary side will force the drain voltage to zero. Thus, zero voltage switching is very possible, preventing large

capacitive switching losses $\left(P = \frac{1}{2} \times C \times V^2 \times f\right)$, and

allowing high frequency operation, which results in small and cost effective inductors.

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Over Current Protection (OCP)

The cycle-by-cycle peak drain current limit circuit uses the external source resistor to measure the current accurately. This allows optimum size determination of the transformer core (cost issue). The circuit is activated after the leading edge blanking time, t_{leb}. The OCP protection circuit limits the 'sense' voltage to an internal level.

OverPower Protection (OPP)

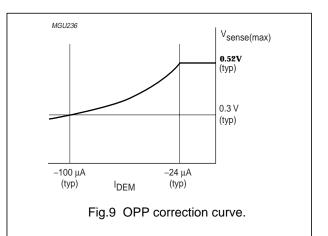
During the primary stroke, the rectified mains input voltage is measured by sensing the current drawn from pin DEM. This current is dependent on the mains voltage, according to the following formula:

$$I_{(DEM)} \approx \frac{V_{aux}}{R_{DEM}} \approx \frac{N \times V_{mains}}{R_{DEM}}$$

Where: N = $\frac{N_{aux}}{N_{p}}$

The current information is used to adjust the peak drain current, which is measured via pin I_{sense}. The internal compensation is such that an almost mains independent maximum output power can be realized.

The OPP curve is given in Fig.9.



Minimum and maximum 'on-time'

The minimum 'on-time' of the SMPS is determined by the Leading Edge Blanking (LEB) time. The IC limits the 'on-time' to 50 μ s. When the system desires an 'on-time' longer than 50 μ s, a fault condition is assumed (e.g. removed C_i), the IC will stop switching and enter the safe restart mode.

Short winding protection

After the leading edge blanking time, the short winding protection circuit is also activated. If the 'sense' voltage exceeds the short winding protection voltage V_{swp} , the converter will stop switching. Once V_{CC} drops below the UVLO level, capacitor C_{VCC} will be recharged and the supply will restart again. This cycle will be repeated until the short circuit is removed (safe restart mode).

The short winding protection will also protect in case of a secondary diode short circuit.

LOCK input

Pin 12 is a general purpose (high impedance) input pin, which can be used to switch off the IC. As soon as the voltage on this pin is raised above 2.5 volts, switching will stop immediately. The voltage on the Vcc pin will cycle between $V_{CC(start)}$ and $V_{CC(UVLO)}$, but the IC will not start switching again until the latch function is reset. The latch is reset as soon as the Vcc drops below 4.5V (typical value). The internal OVP and OTP will also trigger this latch (see also Fig. 2.).

The detection level of this input is related to the V_{CC}5V pin voltage in the following way: $0.5^*V_{CC}5V + -4\%$. An internal zener clamp of 5.6V will protect this pin from excessive voltages. No internal filtering is done on this input.

Overtemperature protection

An accurate temperature protection is provided in the circuit. When the junction temperature exceeds the thermal shutdown temperature, the IC will stop switching. When V_{CC} drops to UVLO, capacitor C_{VCC} will be recharged to the V_{start} level, however the IC will not start switching again. Subsequently, V_{CC} will drop again to the UVLO level, etc..

Operation only recommences when the Vcc voltage drops below a level of about 4.5 V (practically when the Vmains has been disconnected for a short period).

Soft start-up (pin I_{sense})

To prevent transformer rattle during hiccup, the transformer peak current is slowly increased by the soft start function. This can be achieved by inserting a resistor and a capacitor between pin I_{sense} (pin 2) and the sense resistor. An internal current source charges the capacitor to V = I_{ss} × R_{ss}, with a maximum of about 0.5 V.

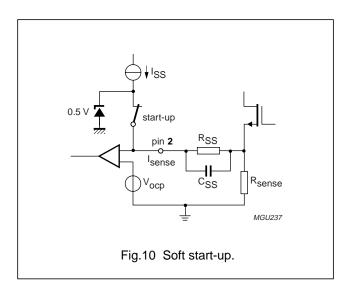
The start level and the time constant of the increasing primary current level can be adjusted externally by changing the values of R_{ss} and C_{ss} .

$$I_{primary(max)} = \frac{V_{ocp} - (I_{ss} \times R_{ss})}{R_{sense}}$$

 $\tau = R_{ss} \times C_{ss}$

The charging current I_{ss} will flow as long as the voltage on pin I_{sense} is below approximately 0.5 V. If the voltage on pin I_{sense} exceeds the 0.5 V, the soft start current source will start limiting the current I_{ss} . At the $V_{CC(start)}$ level, the I_{ss} current source is completely switched off (see Fig.10).

Since the soft start current I_{ss} is subtracted from pin V_{CC} charging current, the R_{ss} value will affect the V_{CC} charging current level by a maximum of 60 μ A (typical value).



5V Output

Pin 11 can be used for supply of external circuitry. The maximum output current must be limited to 1mA. If higher peak currents are required, an external RC combination should limit the current drawn from this pin to 1mA maximum.

The 5V output voltage will be available as soon as the start-up voltage is reached. As the high voltage supply can not supply the 5V pin during start-up and/or shutdown, during latched shutdown (via pin 12 or other latched protection such as OVP or OTP), the voltage is switched to zero.

Driver

The driver circuit to the gate of the power MOSFET has a current sourcing capability of typically 170 mA and a current sink capability of typical 700 mA. This permits fast turn-on and turn-off of the power MOSFET for efficient operation. A low driver source current has been chosen to limit the $\Delta V/\Delta t$ at switch-on. This reduces Electro Magnetic Interference (EMI) and also limits the current spikes across R_{sense}.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134). All voltages are measured with respect to ground (pin 10); positive currents flow into the chip; pin 8 may not be current driven. The voltage ratings are valid provided other ratings are not violated; current ratings are valid provided the maximum power rating is not violated.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Voltages	-	1			
V ₁	pin 1 (VCOadj)	continuous	-0.4	+5	V
V ₂	pin 2 (I _{sense})	current limited	-0.4	_	V
V ₇	pin 7 (DRAIN)		-0.4	+650	V
V ₈	pin 8 (V _{CC})	continuous	-0.4	+20	V
V ₁₂	pin 12 (LOCK)	continuous	-0.4	+7	V
V ₁₃	pin 13 (CTRL)		-0.4	+5	V
V ₁₄	pin 14 (DEM)	current limited	-0.4	_	V
Currents				-	
l ₂	pin 2 (I _{sense})		-1	+10	mA
l ₃	pin 3 (STDBY)		-1	_	mA
I ₄	pin 4 (DRIVER)	d < 10%	-0.8	+2	A
1 ₇	pin 7 (DRAIN)		-	+5	mA
I ₁₁	pin 11 (V _{CC} 5V)		-1	0	mA
I ₁₃	pin 13 (CTRL)		-	+5	mA
I ₁₄	pin 14 (DEM)		-250	+250	μA
General	-			•	
P _{tot}	total power dissipation	T _{amb} < 70 °C	-	0.75	W
T _{stg}	storage temperature		-55	+150	°C
T _{vj}	virtual junction temperature		-20	+145	°C
ESD					
V _{ESD}	electrostatic discharge voltage	class 1			
	human body model	pins 1 to 6 & pins 9 to 14; note 1	-	2000	V
		pin 7 (DRAIN); note 1	-	1500	V
	machine model	note 2	-	400	V

Notes

- 1. Equivalent to discharging a 100 pF capacitor through a 1.5 k Ω series resistor.
- 2. Equivalent to discharging a 200 pF capacitor through a 0.75 μH coil and a 10 Ω resistor.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; note 1	100	K/W

Note

1. With pin GND connected to sufficient copper area on the printed-circuit board.

QUALITY SPECIFICATION

In accordance with 'SNW-FQ-611-E'.

CHARACTERISTICS

 T_{amb} = 25 °C; V_{CC} = 15 V; all voltages are measured with respect to ground (pin 10); currents are positive when flowing into the IC; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Start-up currei	nt source (pin 7)					1
I _{i(DRAIN)}	supply current drawn from drain pin	$V_{CC} = 0 \text{ V}; \text{ V}_{DRAIN} > 100 \text{ V}$	1.0	1.2	1.4	mA
		with auxiliary supply; V _{DRAIN} > 100 V	-	100	300	μA
BV _{DSS}	breakdown voltage		650	-	-	V
M-level	mains-dependent operation-enabling level		60	-	100	V
V _{CC} manageme	ent (pin 8)				•	
V _{CC(start)}	start-up voltage on V _{CC}		10.3	11	11.7	V
V _{CC(UVLO)}	under voltage lock-out on V _{CC}		8.1	8.7	9.3	V
V _{CC(hys)}	hysteresis voltage on V _{CC}	V _{CC(start)} – V _{CC(UVLO)}	2.0	2.3	2.6	V
I _{i(VCC)H}	pin V _{CC} charging current	V _{DRAIN} > 100 V; V _{CC} < 3V	-1.2	-1	-0.8	mA
I _{i(VCC)L}	pin V_{CC} charging current	$V_{\text{DRAIN}} > 100 \text{ V};$ 3 V < V _{CC} < V _{CC(UVLO)}	-1.2	-0.75	-0.45	mA
I _{VCC(restart)}	pin V _{CC} restart current	$V_{DRAIN} > 100 V;$ $V_{CC(UVLO)} < V_{CC} < V_{CC(start)}$	-650	-550	-450	μA
I _{CC(operate)}	supply current under normal operation	no load on pin DRIVER	1.1	1.3	1.5	mA
Demagnetizati	on management (pin 14)					-
V _{DEM}	demagnetization comparator threshold voltage on pin DEM		50	100	150	mV
I(PROT)(DEM)	pin DEM protection current	V _{DEM} = 50 mV	-50 ⁽¹⁾	-	-10	nA
V _{clamp(DEM)(neg)}	negative clamp voltage on pin DEM	at I _{DEM} = –150 μA	-0.5	-0.25	-0.05	V
V _{clamp(DEM)(pos)}	positive clamp voltage on pin DEM	at I _{DEM} = 250 μA	0.5	0.7	0.9	V
t _{suppr}	suppression of transformer ringing at start of secondary stroke		1.1	1.5	1.9	μs
Pulse width me	odulator		•	•	•	
t _{on(min)}	minimum on-time		-	t _{leb}	-	ns
t _{on(max)}	maximum on-time	latched	40	50	60	μs

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Oscillator		1		1		1
f _{oscL}	oscillator low frequency (fixed frequency)	V _{CTRL} > 1.5 V	20	25	30	kHz
f _{oscH}	oscillator high frequency (fixed frequency)	V _{CTRL} < 1 V	100	125	150	kHz
V _{vco(start)}	peak voltage at pin I _{sense} , where frequency reduction starts	see Fig.6 and Fig.7	-	VCO ₁	-	mV
V _{vco(max)}	peak voltage at pin I_{sense} , where the frequency is equal to f_{oscL}		-	VCO ₁ -25	-	mV
Duty cycle co	ntrol (pin 13)	•	·			
V _{CTRL(min)}	min. voltage on CTRL (max. duty cycle)		-	1.0	_	V
V _{CTRL(max)}	max. voltage on CTRL (min. duty cycle)		_	1.5	-	V
5V Output (pi	n 11)				•	
V(V _{CC} 5V)	output voltage	@1 mA	4.75	5.0	5.25	V
I(V _{CC} 5V)	current capability of pin V _{CC} 5V		-1.0		-	mA
LOCK input (pin 12)	·	•			
V _{LOCK}	LOCK trip level		2.37	2.5	2.63	V
V _{CC,RESET}	voltage level on pin V_{CC} which resets the latch	V _{LOCK} <2.3V	-	4.5	-	V
REL _{LOCK,5V}	relation to 5V output (pin 4)	V _{LOCK} =0.5*V _{CC} 5V	-4	_	+4	%
VCOadj input	(pin 1)					
V _{VCO,ACC}	input comparator accuracy		-	t.b.f.	-	%
Valley switch	(pin 7)					
$\Delta V / \Delta t_{valley}$	$\Delta V/\Delta t$ for valley recognition		-85	-	+85	V/µs
t _{valley-swon}	delay from valley recognition to switch-on		_	150 ⁽¹⁾	-	ns
	short winding protection (pin 2)					
V _{sense(max)}	maximum source voltage OCP	$\Delta V/\Delta t = 0.1 V/\mu s$	0.48	0.52	0.56	V
tpropagation	delay from detecting V _{sense(max)} to switch-off	$\Delta V/\Delta t = 0.5 V/\mu s$	-	140	185	ns
V _{swp}	short winding protection voltage		0.83	0.88	0.96	V
t _{leb}	blanking time for current and short winding protection		300	370	440	ns
l _{ss}	soft start current	V _{sense} < 0.5 V	45	60	75	μA
Overvoltage p	protection (pin 14)					
I(OVP)(DEM)	$\begin{array}{c} \mbox{OVP protection level at pin 14, set by the} \\ \mbox{demagnetization resistor } R_{\text{DEM}} \mbox{; see} \\ \mbox{Section "Over Voltage Protection (OVP)"} \end{array}$		54	60	66	μA

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Overpower pr	otection (pin 14)				1	
I _{(OPP)(DEM)}	OPP current at pin 14, start of OPP correction. Set by the demagnetization resistor R_{DEM} ; see Section "OverPower Protection (OPP)"		_	-24	-	μA
I _(OPP50%) (DEM)	OPP current at pin 14 where maximum source voltage is limited to 0.3 V		-	-100	-	μA
STDBY output	t (pin 3)					
V _{STDBY}	STDBY output voltage		4.75	5.0	5.25	V
ISTDBY,SOURCE	pin STDBY current source capability	@ V _{STDBY} =1 V	20	22	24	μA
I _{STDBY,SINK}	pin STDBY current sink capability	@ V _{STDBY} =1 V	2			mA
Driver (pin 4)					•	
Isource	source current capability of driver	V _{CC} = 9.5 V; V _{DRIVER} = 2 V	-	-170	-88	mA
l _{sink}	sink current capability of driver	V _{CC} = 9.5 V; V _{DRIVER} = 2 V	-	300	-	mA
		V _{CC} = 9.5 V; V _{DRIVER} = 9.5 V	400	700	-	mA
V _{o(driver)(max)}	maximum output voltage of the driver	V _{CC} > 12 V	_	11.5	12	V
Temperature p	protection		•	•		
T _{prot(max)}	maximum temperature threshold		130	140	150	°C
T _{prot(hyst)}	hysteresis temperature		_	8(1)	_	°C

Note

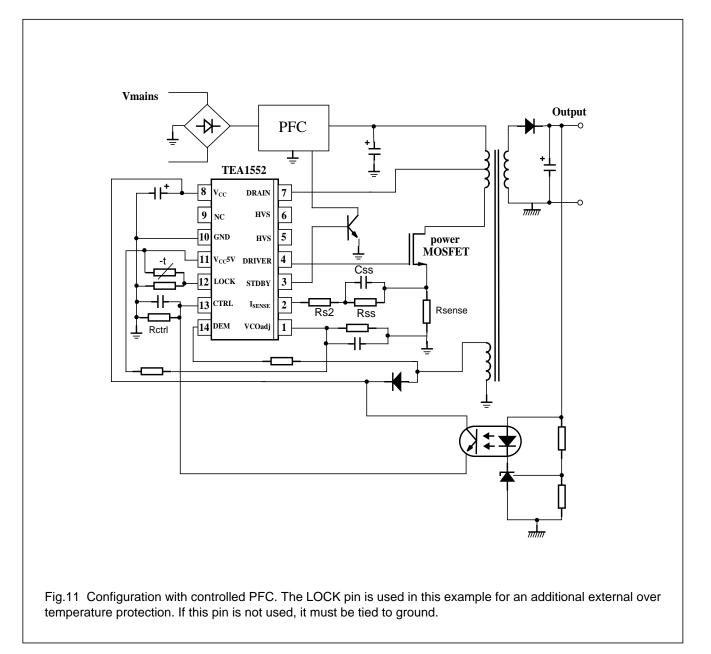
1. Guaranteed by design.

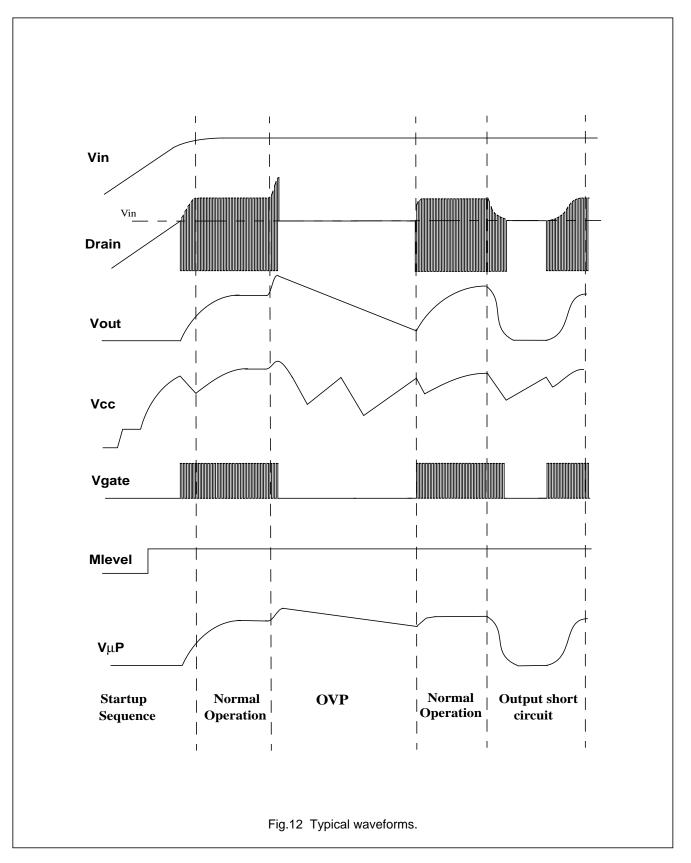
APPLICATION INFORMATION

A converter with the TEA1552 consists of an input filter, a transformer with a third winding (auxiliary), and an output stage with a feedback circuit.

Capacitor C_{VCC} (at pin 8) buffers the supply voltage of the IC, which is powered via the high voltage rectified mains during start-up and via the auxiliary winding during operation.

A sense resistor converts the primary current into a voltage at pin I_{sense} (pin 2). The value of this sense resistor defines the maximum primary peak current.

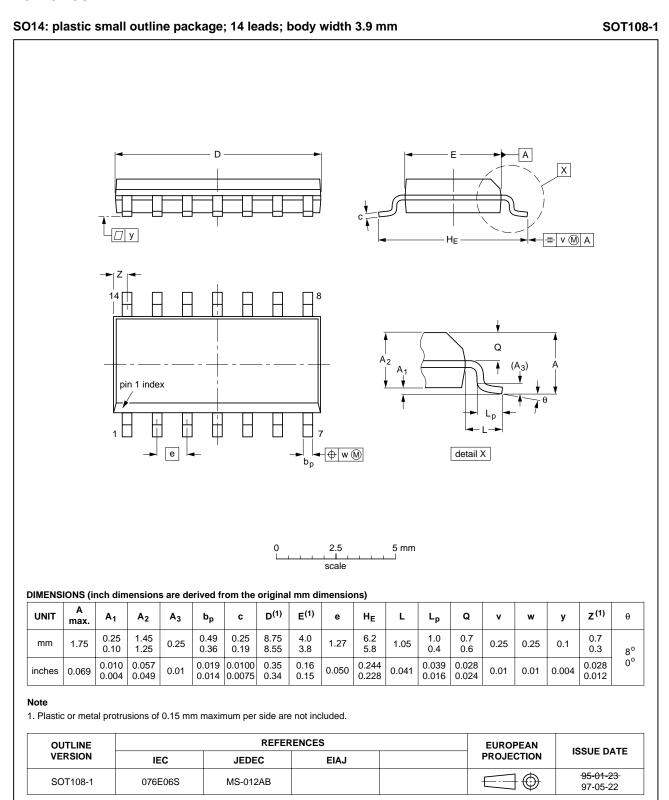




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GreenChip™II SMPS control IC

PACKAGE OUTLINE



SOLDERING

Introduction

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mount components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

Through-hole mount packages

SOLDERING BY DIPPING OR BY SOLDER WAVE

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joints for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ($T_{stg(max)}$). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

MANUAL SOLDERING

Apply the soldering iron (24 V or less) to the lead(s) of the package, either below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

Surface mount packages

REFLOW SOLDERING

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method. Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

WAVE SOLDERING

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

MANUAL SOLDERING

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

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When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

Suitability of IC packages for wave, reflow and dipping soldering methods

MOUNTING	PACKAGE	SOLDERING METHOD			
MOONTING	PACKAGE	WAVE	REFLOW ⁽¹⁾	DIPPING	
Through-hole mount	DBS, DIP, HDIP, SDIP, SIL	suitable ⁽²⁾	-	suitable	
Surface mount	BGA, LFBGA, SQFP, TFBGA	not suitable	suitable	-	
	HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, SMS	not suitable ⁽³⁾	suitable	-	
	PLCC ⁽⁴⁾ , SO, SOJ	suitable	suitable	-	
	LQFP, QFP, TQFP	not recommended ⁽⁴⁾⁽⁵⁾	suitable	-	
	SSOP, TSSOP, VSO	not recommended ⁽⁶⁾	suitable	_	

Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.
- 2. For SDIP packages, the longitudinal axis must be parallel to the transport direction of the printed-circuit board.
- 3. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is only suitable for LQFP, QFP and TQFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 6. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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